

DOCKET NO. 8543-004-27 CIP



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Marvin LIAO et al.

ART UNIT: 2814

SERIAL NO.: 08/825,360

EXAMINER: Tuan N. Quach

FILING DATE: March 28, 1997

FOR: AN INTERCONNECT STRUCTURE FOR USE IN AN INTEGRATED CIRCUIT

29/E  
6-4-02  
T. Flowers

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Responsive to the outstanding Office Action mailed November 30, 2001, the period for response thereto being extended by virtue of the petition and extension fees filed concurrently herewith, applicant responds as follows.

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IN THE CLAIMS

Please amend claims 21 and 48 as follows:

21. (Thrice Amended) A method for forming a structure in an integrated circuit, said structure extending from a conductive surface through a channel having inner walls extending above said conductive surface, said method including the steps of:

(a) depositing a layer of a refractory metal on said conductive surface and said inner walls of said channel;

(b) forming a layer of metal nitride on said layer of said refractory metal, wherein said layer of said metal nitride has a thickness extending from said layer of said refractory metal of less than 130 Å; and

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